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WEST**Generate Collection****Search Results - Record(s) 1 through 4 of 4 returned.**☐ 1. Document ID: US 5861135 A

L6: Entry 1 of 4

File: USPT

Jan 19, 1999

US-PAT-NO: 5861135

DOCUMENT-IDENTIFIER: US 5861135 A

TITLE: Highly crystalline diamond

DATE-ISSUED: January 19, 1999

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Tanabe; Keiichiro	Hyogo-ken	N/A	N/A	JPX
Fujimori; Naoji	Hyogo-ken	N/A	N/A	JPX

US-CL-CURRENT: 423/446

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Draw Desc	Image
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☐ 2. Document ID: US 5776552 A

L6: Entry 2 of 4

File: USPT

Jul 7, 1998

US-PAT-NO: 5776552

DOCUMENT-IDENTIFIER: US 5776552 A

TITLE: Process for the vapor phase synthesis of diamond and highly crystalline diamond

DATE-ISSUED: July 7, 1998

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Tanabe; Keiichiro	Hyogo-ken	N/A	N/A	JPX
Fujimori; Naoji	Hyogo-ken	N/A	N/A	JPX

US-CL-CURRENT: 427/577; 117/104, 423/446

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Draw Desc	Image
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☐ 3. Document ID: US 5646924 A

L6: Entry 3 of 4

File: USPT

Jul 8, 1997

US-PAT-NO: 5646924

DOCUMENT-IDENTIFIER: US 5646924 A

TITLE: Recording and simultaneous verifying method of phase-changing type of information recording medium

DATE-ISSUED: July 8, 1997

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Nonoyama; Osamu	Yokohama	N/A	N/A	JPX
Ide; Yukio	Mishima	N/A	N/A	JPX
Harigaya; Makoto	Hiratsuka	N/A	N/A	JPX
Kageyama; Yoshiyuki	Yokohama	N/A	N/A	JPX
Deguchi; Hiroshi	Yokohama	N/A	N/A	JPX
Yamada; Katsuyuki	Mishima	N/A	N/A	JPX
Takahashi; Masaetsu	Yokohama	N/A	N/A	JPX
Iwasaki; Hiroko	Tokyo	N/A	N/A	JPX

US-CL-CURRENT: 369/53.36; 369/116, 369/275.1

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Draw Desc	Image
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☐ 4. Document ID: US 5270263 A

L6: Entry 4 of 4

File: USPT

Dec 14, 1993

US-PAT-NO: 5270263

DOCUMENT-IDENTIFIER: US 5270263 A

TITLE: Process for depositing aluminum nitride (AlN) using nitrogen plasma sputtering

DATE-ISSUED: December 14, 1993

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Kim; Sung C.	Boise	ID	N/A	N/A
Yu; Chris C.	Boise	ID	N/A	N/A
Doan; Trung T.	Boise	ID	N/A	N/A

US-CL-CURRENT: 438/702; 204/192.22, 204/192.25, 438/717, 438/740, 438/761

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Draw Desc	Image
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Terms	Documents
((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmK)	4

Documents, starting with Document:

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Terms	Documents
((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	0

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(thermal adj conductivity) and (w/cmk)[Clear](#)**Search History**

Today's Date: 3/13/2001

<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	0	<u>L7</u>
USPT	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	4	<u>L6</u>
JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	0	<u>L5</u>
PGPB,JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w adj cmk)	0	<u>L4</u>
PGPB,JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w adj cm adj k)	0	<u>L3</u>
PGPB,JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity)	656	<u>L2</u>
PGPB	semiconductor	0	<u>L1</u>

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Terms	Documents
((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and semiconductor	57

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((aluminum adj nitride) or aln) and
(carbon or c or oxygen or o or oxide or
carbide) and glass and substrate and

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Today's Date: 3/13/2001

<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and semiconductor	57	<u>L5</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or oxygen or o or oxide or carbide) and glass and substrate	124	<u>L4</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and transistor	3	<u>L3</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate	244	<u>L2</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide)	5301	<u>L1</u>

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Terms	Documents
(alnc or alcn or (al adj c adj n) or (al adj n adj c))	26

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(alnc or alcn or (al adj c adj n) or (al adj n adj c))	▲
	▬
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<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
JPAB	(aln c or alcn or (al adj c adj n) or (al adj n adj c))	26	L14
JPAB	(aln c or alcn or (al adj c adj n) or (al adj n adj c)) and glass and substrate	0	L13
JPAB	((aluminum adj (carb\$ or \$nitride)) or aln c or alcn or (al adj c adj n) or (al adj n adj c)) and glass and substrate and semiconductor	32	L12
JPAB	((aluminum adj (carb\$ or \$nitride)) or aln c or alcn or (al adj c adj n) or (al adj n adj c)) and glass and substrate	118	L11
JPAB	((aluminum adj oxynitride) or alno or alon or (al adj o adj n) or (al adj n adj o)) and glass and substrate	9	L10
JPAB	((aluminum adj oxynitride) or alno or alon) and glass and substrate	2	L9
JPAB	(aluminum adj oxynitride) or alno or alon and glass and substrate and semiconductor	75	L8
JPAB	(aluminum adj oxynitride) or alno or alon and glass and substrate	75	L7
JPAB	(aluminum adj oxynitride) or alno or alon	131	L6
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and semiconductor	57	L5
JPAB	((aluminum adj nitride) or aln) and (carbon or oxygen or o or oxide or carbide) and glass and substrate	124	L4
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and transistor	3	L3
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate	244	L2
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide)	5301	L1